

## عنوان مقاله:

Effective Channel Length Extraction of MOS Transistors with Halo/Pocket Implants

## محل انتشار:

دوازدهمین کنفرانس مهندسی برق ایران (سال: 1383)

تعداد صفحات اصل مقاله: 5

## نویسندگان:

E. Fathi - Device Simulation Laboratory, ECE Department, University of Tehran

B Afzal

M Fathipour

## خلاصه مقاله:

The shift-and-Ratio method has been considered as one of the most accurate and consistent techniques for extracting the effective channel-length of the MOS transistors. The use of original shift-and-ratio method for  $L_{eff}$  extraction of MOS transistors with halo/pocket implants results in systematic errors for  $L_{eff}$ . In this paper a modification of the original method has been proposed and tested by simulation. The values of  $L_{eff}$  generated by this method are more reasonable than the original shift-and-ratio method.

## کلمات کلیدی:

Effective channel length, halo/pocket implant, parameter extraction, shift-and-ratio method

## لینک ثابت مقاله در پایگاه سیویلیکا:

<https://civilica.com/doc/59996>

